

# An Ultra-small 1.4 mm<sup>2</sup>, 18 m $\Omega$ , 2.0 A Integrated Power Switch with Discharge

#### **General Description**

The SLG59M1720V is a high performance 18 m $\Omega$ , 2.0 A single-channel nFET integrated power switch which can operate with a 2.5 V to 3.6 V V<sub>DD</sub> supply to switch power rails from as low as 0.85 V up to the supply voltage. The SLG59M1720V incorporates two-level overload current protection, thermal shutdown protection, fast output discharge, and in-rush current control which can easily be adjusted by a small external capacitor.

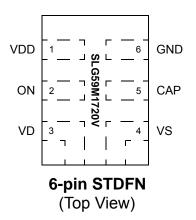
Using a proprietary MOSFET design, the SLG59M1720V achieves a stable 18 m $\Omega$  RDSON across a wide input voltage range and over temperature. In addition, the SLG59M1720V's package also exhibits low thermal resistance for high-current operation using Silego's proprietary CuFET technology.

Fully specified over the -40 °C to 85 °C temperature range, the SLG59M1720V is packaged in a space-efficient, low thermal resistance, RoHS-compliant 1.0 mm x 1.4 mm STDFN package.

#### Features

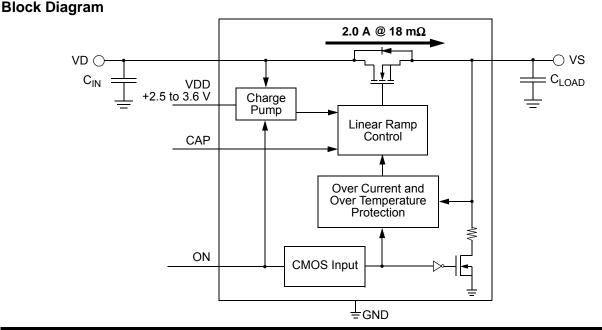
- Low RDS<sub>ON</sub> nFET: 18 m $\Omega$
- Steady-state Operating Current: Up to 2.0 A
- Supply Voltage:  $2.5 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.6 \text{ V}$
- Wide Input Voltage Range: 0.85 V ≤ V<sub>D</sub> ≤ V<sub>DD</sub>
- Capacitor-programmable Start-up and Inrush Current Control
- Two-stage Overcurrent Protection:
  - Fixed 2.6 A Active Current Limit
  - · Fixed 0.5 A Short-circuit Current Limit
- Thermal Shutdown Protection
- Fast VOUT Discharge
- Operating Temperature: -40 °C to 85 °C
- Low θ<sub>JA</sub>, 6-pin 1.0 mm x 1.4 mm STDFN Packaging
  Pb-Free / Halogen-Free / RoHS compliant





#### Applications

- GPS Devices
- Notebook & Tablet PCs
- Smartphones
- Portable Consumer Electronics
- Portable Bar-Code Scanners
- Portable POS Terminals





#### **Pin Description**

Pin #	Pin Name	Туре	Pin Description
1	VDD	Power	With an internal 1.9V UVLO threshold, VDD supplies the power for the operation of the power switch and internal control circuitry. Bypass the VDD pin to GND with a $0.1\mu$ F (or larger) capacitor.
2	ON	Input	A low-to-high transition on this pin initiates the operation of the SLG59M1720V's state machine. ON is an asserted HIGH, level-sensitive CMOS input with V <sub>IL</sub> <0.3 V and V <sub>IH</sub> >0.85V. While there is an internal pull-down circuit to GND (~4M $\Omega$ ), connect this pin directly to a general-purpose output (GPO) of a microcontroller, an application processor, or a system controller – do not allow this pin to be open-circuited.
3	VD	MOSFET	Drain terminal connection of the n-channel FET. Connect a $10-\mu F$ (or larger) low-ESR capacitor from this pin to ground. Capacitors used at VD should be rated at 10 V or higher.
4	VS	MOSFET	Source terminal connection of the n-channel FET. Connect a 10 $\mu$ F (or larger) low-ESR capacitor from this pin to ground. Capacitors used at VS should be rated at 10 V or higher. To speed up VS fall time on OFF, the SLG59M1720V includes a 220 $\Omega$ discharge path to GND.
5	САР	Output	A low-ESR, stable dielectric, ceramic surface-mount capacitor connected from CAP pin to GND sets the VS slew rate and overall turn-on time of the SLG59M1720V. For best performance, the range for CAP values are 1 nF $\leq$ CAP $\leq$ 22 nF. Capacitors used at CAP should be rated at 10 V or higher.
6	GND	GND	Ground connection. Connect this pin to system analog or power ground plane.

#### **Ordering Information**

Part Number	Туре	Production Flow
SLG59M1720V	STDFN 6L	Industrial, -40 °C to 85 °C
SLG59M1720VTR	STDFN 6L (Tape and Reel)	Industrial, -40 °C to 85 °C



#### **Absolute Maximum Ratings**

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply				4.5	V
Τ <sub>S</sub>	Storage Temperature		-65		150	°C
ESD <sub>HBM</sub>	ESD Protection	Human Body Model	2000			V
ESD <sub>CDM</sub>	ESD Protection	Charged Device Model	1000			V
MSL	Moisture Sensitivity Level				1	
$\theta_{JA}$	Thermal Resistance	$1.0 \times 1.4 \text{ mm } 6L \text{ STDFN}$ ; Determined using 1 in <sup>2</sup> , 1 oz. copper pads under VD and VS terminals and FR4 pcb material		72		°C/W
W <sub>DIS</sub>	Package Power Dissipation				0.4	W
MOSFET IDS <sub>PK</sub>	Peak Current from Drain to Source	Maximum pulsed switch current, pulse width < 1ms, 1% duty cycle			3	Α
only and fu	nctional operation of the device at thes	Maximum Ratings" may cause permanent damages or any other conditions above those indicates aximum rating conditions for extended periods r	ed in the	operatior	nal sectior	

#### **Electrical Characteristics**

 $T_A$  = -40 °C to 85 °C (unless otherwise stated)

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply Voltage	-40 °C to 85 °C	2.5		3.6	V
1	Dower Supply Current (DIN 1)	when OFF			1	μA
I <sub>DD</sub>	Power Supply Current (PIN 1)	when ON, No load		85	100	μA
200	Static Drain to Source	T <sub>A</sub> 25°C @ 100 mA		18	21	mΩ
RDS <sub>ON</sub>	ON Resistance	T <sub>A</sub> 85°C @ 100 mA		20	24	mΩ
IDS	Operating Current	V <sub>D</sub> = 1.0 V to 3.6 V			2.0	Α
I <sub>FET_OFF</sub>	MOSFET OFF Leakage Current	V <sub>D</sub> = 3.3 V, V <sub>S</sub> = 0 V; ON = LOW			1	μA
V <sub>D</sub>	Drain Voltage		0.85		V <sub>DD</sub>	V
T <sub>ON_Delay</sub>	ON pin Delay Time	50% ON to Ramp Begin, R <sub>LOAD</sub> = 100 Ω, no C <sub>LOAD</sub>		450	650	μs
		50% ON to 90% V <sub>S</sub>	Configurable <sup>1</sup>			ms
T <sub>Total_ON</sub>	Total Turn On Time	Example: CAP (PIN 5) = 4 nF, $V_{DD} = V_D = 3.3 V$ , $R_{LOAD} = 100 \Omega$ , $C_{LOAD} = 10 \mu F$		1.4	1.7	ms
		10% V <sub>S</sub> to 90% V <sub>S</sub>	Co	onfigurable	e <sup>1</sup>	V/ms
T <sub>SLEWRATE</sub>	Slew Rate	Example: CAP (PIN 5) = 4 nF, $V_{DD} = V_D = 3.3 V$ , $R_{LOAD} = 100 \Omega$ , $C_{LOAD} = 10 \mu F$	2.5	3.0	3.5	V/ms
T <sub>OFF_Delay</sub>	OFF Delay Time	50% ON to V <sub>S</sub> Fall, V <sub>DD</sub> = V <sub>D</sub> = 3.3 V, R <sub>LOAD</sub> = 100 Ω, no C <sub>LOAD</sub>		3.2		μs
T <sub>FALL</sub>	V <sub>S</sub> Fall Time	90% V <sub>S</sub> to 10% V <sub>S</sub> , V <sub>DD</sub> = V <sub>D</sub> = 3.3 V, R <sub>LOAD</sub> = 100 Ω, no C <sub>LOAD</sub>		0.5		μs
C <sub>LOAD</sub>	Output Load Capacitance	$C_{LOAD}$ connected from V <sub>S</sub> to GND	10	22	100	μF
R <sub>DIS</sub>	Discharge Resistance		150	220	300	Ω

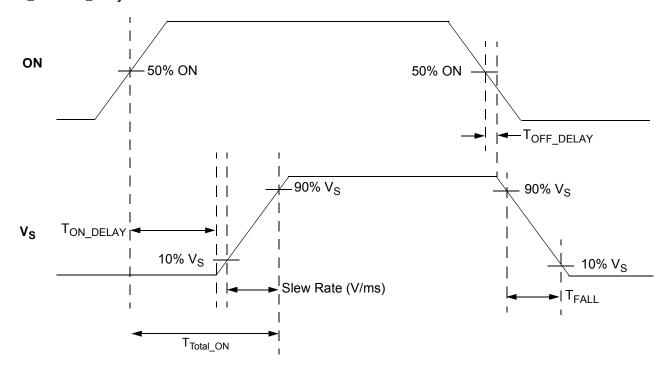


#### Electrical Characteristics (continued)

 $T_A$  = -40 °C to 85 °C (unless otherwise stated)

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
ON_V <sub>IH</sub>	High Input Voltage on ON pin		0.85		V <sub>DD</sub>	V
$ON_V_{IL}$	Low Input Voltage on ON pin		-0.3	0	0.3	V
1	Active Current Limit	MOSFET will automatically limit current when $V_S > 250 \text{ mV}$	2.1	2.6	3.1	А
ILIMIT	Short Circuit Current Limit	MOSFET will automatically limit current when $V_S$ < 250 mV		0.5		А
THERMON	Thermal shutoff turn-on temperature			135		°C
THERMOFF	Thermal shutoff turn-off temperature			105		°C
THERM <sub>TIME</sub>	Thermal shutoff time				1	ms
Notes: 1. Refer to ta	able for configuration details.					

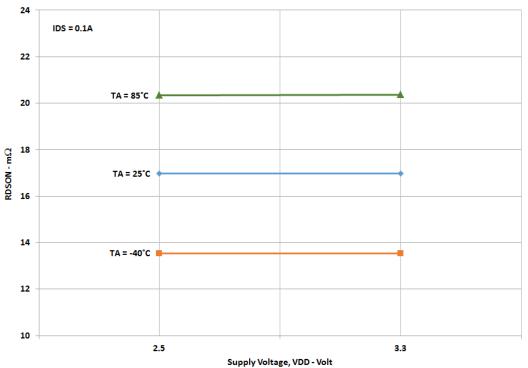
### T<sub>Total\_ON</sub>, T<sub>ON\_Delay</sub> and Slew Rate Measurement

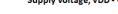


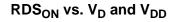


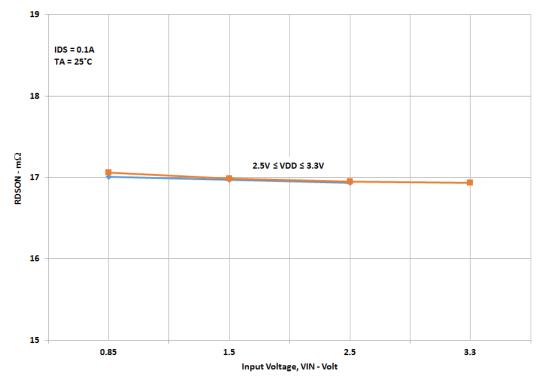
#### **Typical Performance Characteristics**

#### $\text{RDS}_{\text{ON}}$ vs. $\text{V}_{\text{DD}},$ and Temperature



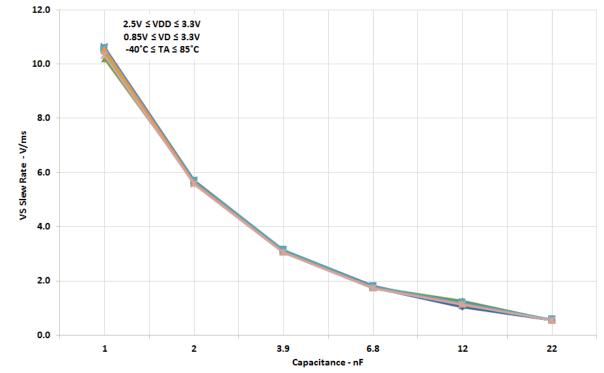




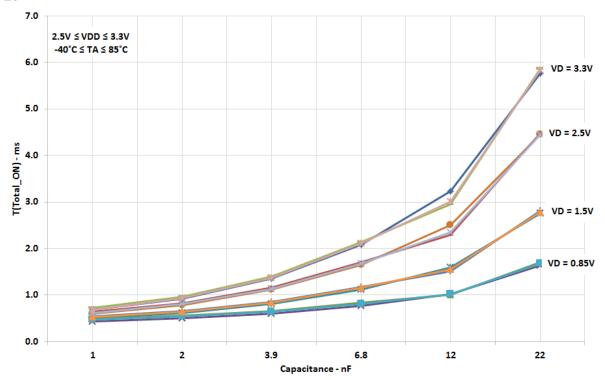








 $T_{Total\_ON}$  vs. CAP,  $V_D,\,V_{DD},\,and$  Temperature





#### SLG59M1720V Power-Up/Power-Down Sequence Considerations

A nominal power-up sequence is to apply  $V_{DD}$  first, followed by  $V_D$  only after  $V_{DD}$  is > 1.9 V, and finally toggling the ON pin LOW-to-HIGH after  $V_D$  is at least 90% of its final value.

A nominal power-down sequence is the power-up sequence in reverse order. It is important that the SLG59M1720V's ON pin is toggled HIGH only after  $V_{DD}$  and  $V_D$  have reached their steady-state values; otherwise, the power switch will spend an undesirable amount of time in high-resistance mode while powering up, heating up, and possibly reaching its thermal shutdown before ever fully turning on.

If  $V_{DD}$  and  $V_D$  are applied at the same time, a voltage glitch may appear on the output pin at  $V_S$ . To prevent glitches at the output, it is recommended to connect a 10  $\mu$ F capacitor from the  $V_S$  pin to GND and to keep the  $V_{DD}$  &  $V_D$  ramp times less than 2 ms.

The V<sub>S</sub> output follows a linear ramp when the power switch is turned on, provided that the V<sub>S</sub> slew time set by CAP is less than the RC time constant formed by the RDS<sub>ON</sub> of the power switch and load capacitance  $C_{LOAD}$ .

#### SLG59M1720V Current Limiting Operation

The SLG59M1720V has two types of current limiting triggered by the output V<sub>S</sub> pin voltage.

#### 1. Standard Current Limiting Mode (with Thermal Shutdown Protection)

When the V<sub>S</sub> pin voltage > 250 mV, the output current is initially limited to the Active Current Limit (ACL) specification listed in the Electrical Characteristics table. The ACL monitor's response time is very fast and is triggered within a few microseconds to sudden (transient) changes in load current. When a load current overload is detected, the ACL monitor increases the FET resistance to keep the current from exceeding the power switch's ACL threshold.

However, if a load-current overload condition persists where the die temperature rises because of the increased FET resistance, the power switch's internal Thermal Shutdown Protection circuit can be activated. If the die temperature exceeds the listed THERM<sub>ON</sub> specification, the FET is shut OFF completely, thereby allowing the die to cool. When the die cools to the listed THERM<sub>OFF</sub> temperature threshold, the FET is allowed to turn back on. This process may repeat as long as the output current overload condition persists.

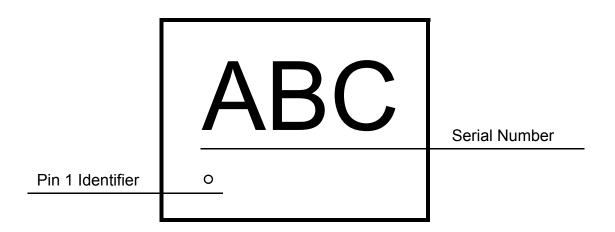
#### 2. Short Circuit Current Limiting Mode (with Thermal Shutdown Protection)

When the  $V_S$  pin voltage < 250 mV (which is the case with a hard short, such as a solder bridge on the power rail), the power switch's internal Short-circuit Current Limit (SCL) monitor limits the FET current to approximately 500 mA (the SCL threshold). While the internal Thermal Shutdown Protection circuit remains enabled and since the SCL threshold is much lower than the ACL threshold, thermal shutdown protection may become activated only at higher ambient temperatures.

For more information on Silego GreenFET3 integrated power switch features, please visit our <u>Application Notes</u> page at our website and see <u>App Note "AN-1068 GreenFET3 Integrated Power Switch Basics"</u>.



#### Package Top Marking System Definition

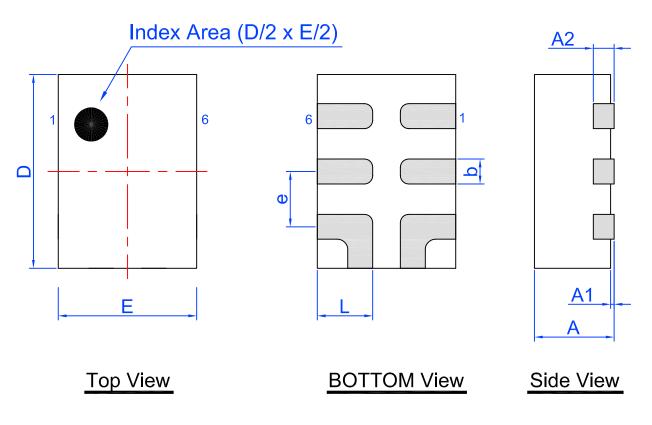


ABC - Part Serial Number Field each A, B, and C character can be A-Z and 0-9



#### Package Drawing and Dimensions

6 Lead STDFN Package 1.0 x 1.4 mm

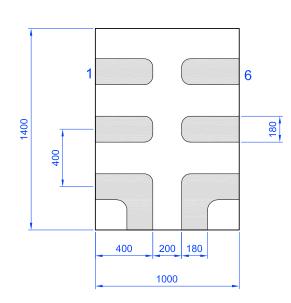


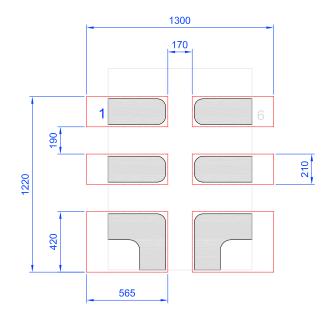
### Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
A	0.50	0.55	0.60	D	1.35	1.40	1.45
A1	0.005	-	0.060	E	0.95	1.00	1.05
A2	0.10	0.15	0.20	L	0.35	0.40	0.45
b	0.13	0.18	0.23	е	0.40 BSC		



#### **Recommended Land Pattern**





# Unit: um

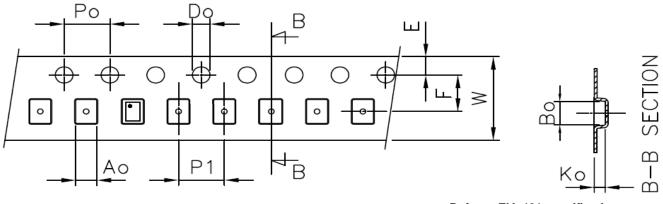


#### **Tape and Reel Specifications**

Bookaga	# of	Nominal	Nominal Max Units		Reel & Lead		r (min)	Trailer (min)		Таре	Part
Package Type	# or Pins	Package Size [mm]	per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STDFN 6L 1x1.4mm 0.4P FC Green	6	1.0 x 1.4 x 0.55	3,000	3,000	178 / 60	100	400	100	400	8	4

#### **Carrier Tape Drawing and Dimensions**

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width
	A0	В0	K0	P0	P1	D0	Е	F	w
STDFN 6L 1x1.4mm 0.4P FC Green	1.21	1.62	0.75	4	4	1.5	1.75	3.5	8



Refer to EIA-481 specification

#### **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 0.77 mm<sup>3</sup> (nominal). More information can be found at www.jedec.org.



#### **Revision History**

Date	Version	Change
2/23/2017	1.00	Production Release